Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO.	SERIAL NO.
		241174US2S	NEW APPLICATION
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT	
		Tadashi MIWA	
		FILING DATE	GROUP
		HEREWITH	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,240,012	05/29/01	H. NAKAMURA, et al.			
	AB	6,353,242	03/05/02	H. WATANABE, et al.			
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO	2002-176114	06/21/02	Japan		x
	AP	2000-22113	01/21/00	Japan		x
	AQ	2003-51557	02/21/03	Japan		x
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	
	AX	
	AY	
	AZ	☐ Additional References sheet(s) attached

Examiner	Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Docket No. 241174US2S

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Tadashi MIWA

SERIAL NO: NEW APPLICATION GAU:

FILED: HEREWITH EXAMINER:

FOR: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

■ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

■ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

■ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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(OSMMN 05/03)

LIST OF RELATED CASES

Docket Number	Serial or Patent Number	Filing or Issue Date	Inventor/ Applicant
PER CLIENT	6,240,012	05/29/01	NAKAMURA et al.
PER CLIENT	6,353,242	03/05/02	WATANABE et al.
214258US2S	09/956,986	09/21/01	MATSUI et al.
223665US2S	10/155,086	05/28/02	ICHIGE et al.

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DOCKET NO: 241174US2S Sheet 1 of 1

IN RE APPLICATION OF: Tadashi MIWA

SERIAL NO: New Application

FILED: Herewith

FOR: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

STATEMENT OF RELEVANCY

Reference AO (JP 2002-176114)) on Form PTO- 1449:

This reference related to NAND flash memory, In the selected gate region and the peripheral circuit region, the insulation film formed on the first electrode layer has the opening.

Reference AP (JP 2000-22113)) on Form PTO- 1449:

The constitution of each first memory cell unit on the end side of a memory cell array is made different from that of each memory cell unit on the end side of the memory cell array.

Reference AQ (JP 2003-51557) on Form PTO- 1449:

This reference is discussed in the specification. See page 3, line 15.